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### Advanced Thermal Control Enabling Cost Reduction for Automotive Power Electronics

Thomas Abraham, Kenneth Kelly, and Kevin Bennion National Renewable Energy Laboratory

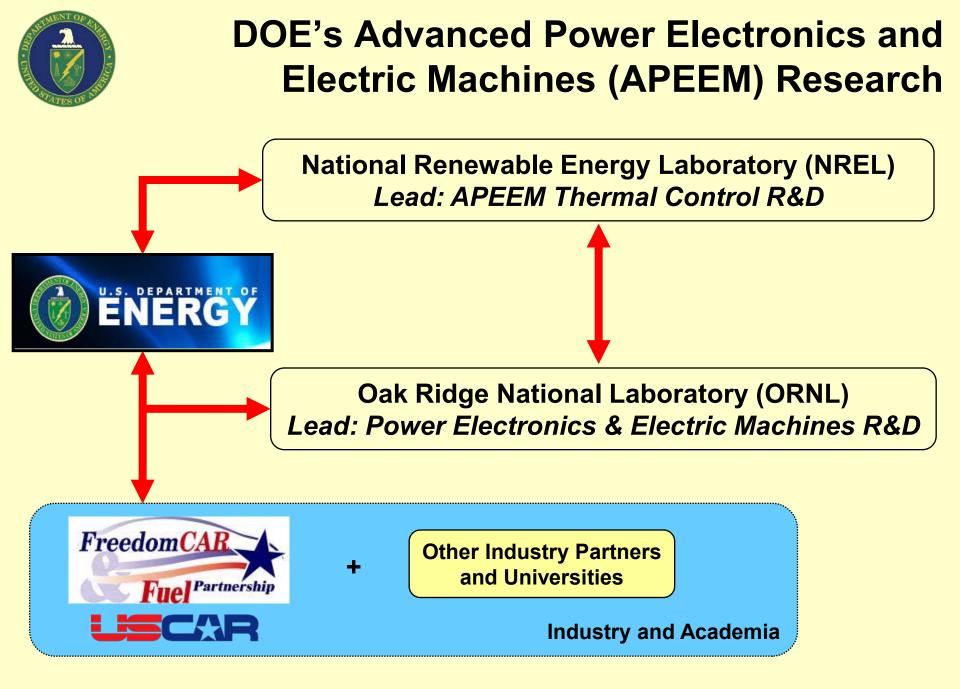
Andreas Vlahinos, Advanced Engineering Solutions, LLC

NREL/PR-540-43819

Presented at the 2008 ANSYS Automotive Conference sponsored by ANSYS held September 4-5, 2008 in Dearborn, Michigan

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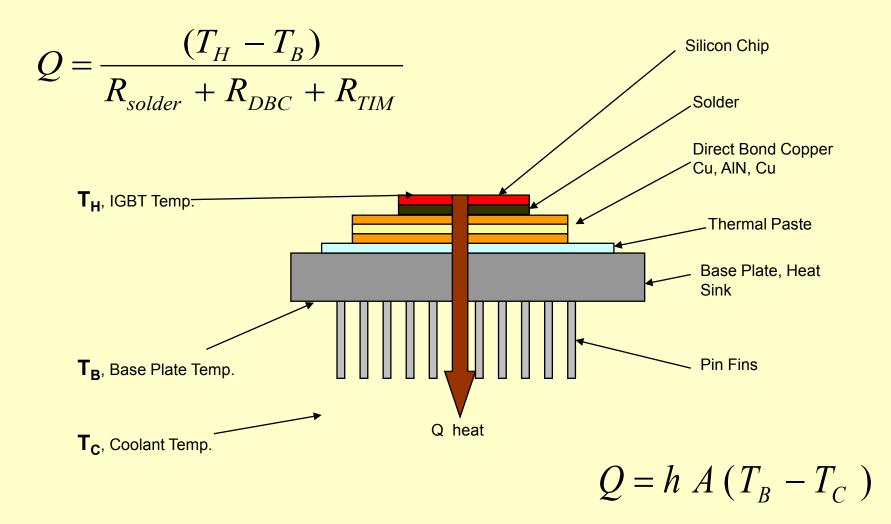
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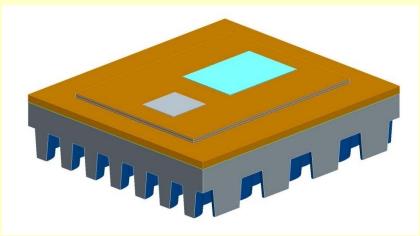
# Motivation

- Most aggressive target of FreedomCAR program is the cost (2020 target is \$8/kW for a 55 kW traction system).
- Meeting the cost target is critical for greater penetration of the vehicles market.
- NREL's Advanced Power Electronics team is working on next-generation advanced cooling technologies (jets/sprays/micro-channels with single or two-phase) and novel packaging topologies.
- Advanced cooling technologies are used in conjunction with novel packaging topologies for identifying low-cost materials for cost (and weight) reductions while meeting the targets of performance and reliability.

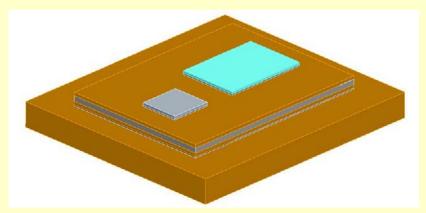
# **Description of Technology**



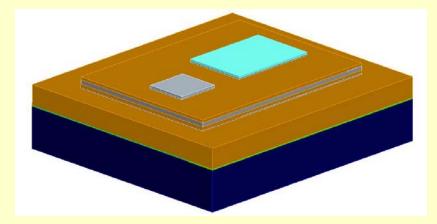
# **Topologies**



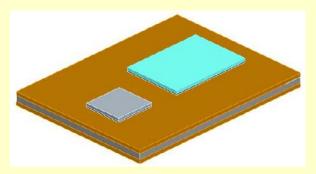
**Baseline Topology** 



Topology 2 (Base plate cooling; does not involve Thermal Interface Material)



Topology 1 (very similar to the baseline topology, which uses Thermal Interface Material)



Topology 3 (Direct Cooling of Direct Bonded Copper)

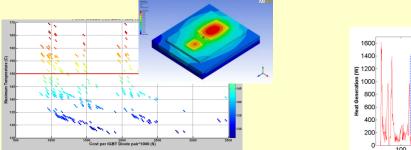
### **Thermal Materials Exploration Study – Steps**

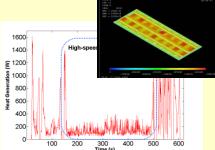
### **Thermal Materials Exploration Study**

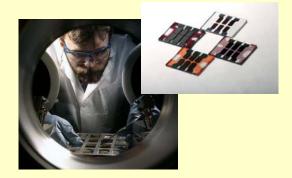
Part 1:

Exploring tradeoffs between thermal performance and cost for several topologies Part 2: Evaluation of Thermal Stress and Reliability Aspects Part 3:

Emerging technologies: 1)LTCC substrates 2)Organic substrates







- Performance: Peak temperatures of the switching devices (IGBTs and diodes) need to be below 150°C.
- Reliability: Power electronics need to meet life-cycle target of 15 years.

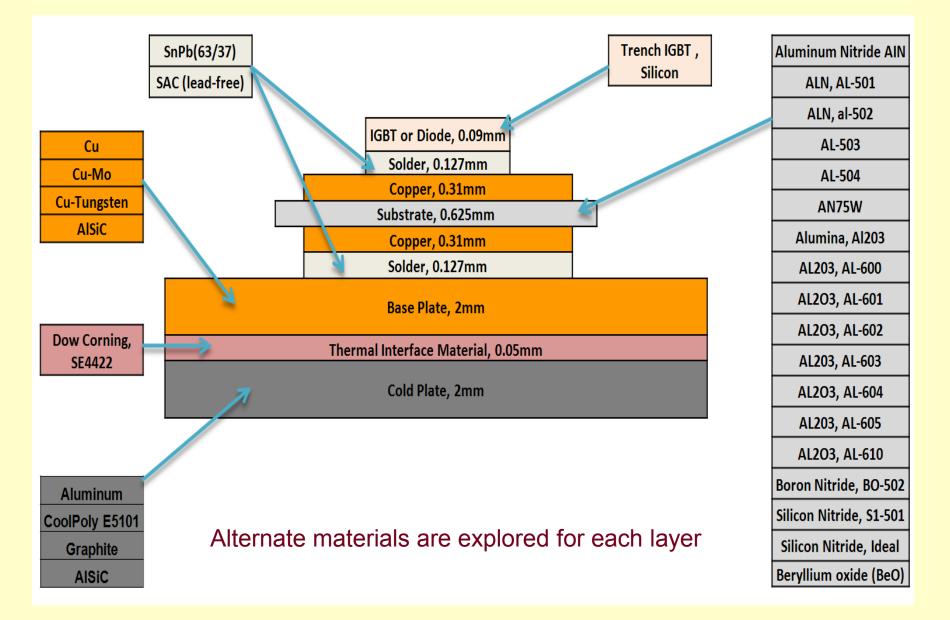
### **Thermal Materials Exploration Study – Comments**

- Two layers that have potential opportunities for cost reduction are the substrate and the cold plate.
- Today's preferred substrate, Aluminum Nitride (AIN) is expensive.
- Low-cost LTCC technology has been well demonstrated in automotive electronics applications. Several issues, notably thermal disadvantages have slowed down the spread of this substrate technology [1].
- Silicon nitride (SiN) as a substrate would make economic sense if the cost is reduced to \$5 per pound [2].

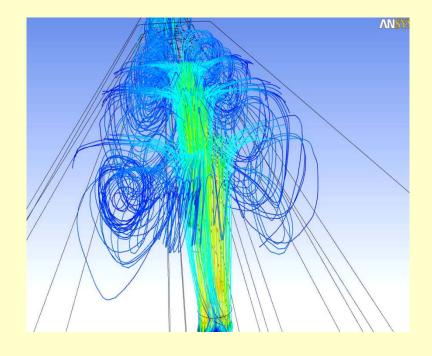
1. Fairchild, M.R., Snyder, R.B., Berlin, C.W., and Sarma, D.H.R., "Emerging Substrate Technologies for Harsh-Environment Automotive Electronics Applications," SAE 2002-01-1052.

2. Das, S., and Curlee, T.R., "The Cost of Silicon Nitride Powder: What Must It Be To Compete?" 1992, ORNL-6694.

# **Materials Exploration – Topology 1**



# Verification of CFD Model with Test





### **CFD (using Fluent)**

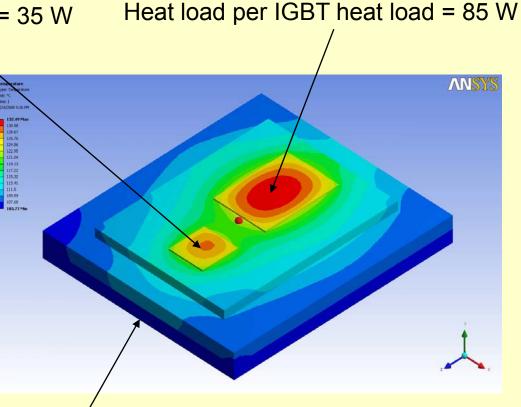


|   | CFD    | Test   |
|---|--------|--------|
| Average Heat<br>Transfer Coefficient<br>(W/m <sup>2</sup> .K) | 18,350 | 18,481 |

### "What-If" option of Design Explorer in "ANSYS Workbench Thermal Simulation" is used to automate materials exploration studies

Heat Load per Diode = 35 W

| ameter Information                                |                                       |                         |                      |                                      |
|---|---------------------------------------|-------------------------|----------------------|--------------------------------------|
| e table below gives information about each parame | ter in the analysis.                  |                         |                      |                                      |
| ameter Name                                       | Source Application                    | Type                    | Neture               | Initial Value                        |
| Plates Themal Conductivity                        | ID EDA                                | input                   | Continuous           | 220                                  |
| ters Themai Conductivity                          | ID EDA                                | Input                   | Continuous           | 38                                   |
| shakis Thermal Conductivity                       | ID_EDA                                | 1.01                    | Continuous           | 170                                  |
| e Plates Thermal Conductivity                     | ID_EDA                                | input                   | Continuous           | 175                                  |
| perature Maximum                                  | Araysis                               | Output                  | Continuous           | 133.64                               |
| an Points   |                                       |                         |                      |                                      |
| 1 70  | <sub>late</sub> k <sub>solder</sub> k | 12                      | 117                  | 19.75                                |
| k <sub>coldp</sub>                                |                                       | tivity                  | y is '               | <sub>eplate</sub>                    |
| Therma<br>for all t                               | l Conduc<br>he layers                 | ctivity<br>acc          | y is v<br>cordi      | <sup>eplate</sup><br>varie<br>ing to |
| Therma<br>for all t                               | l Conduc<br>he layers                 | ctivity<br>acc          | y is v<br>cordi      | varie                                |
| Therma<br>for all t                               | I Conduc                              | ctivity<br>acc          | y is v<br>cordi      | eplate<br>varie                      |
| therma<br>for all the                             | l Conduc<br>he layers                 | ctivity<br>acc          | y is v<br>cordi      | varie                                |
| therma<br>for all the                             | I Conduc<br>he layers<br>the ma       | ctivity<br>acc<br>teria | y is '<br>cordi      | varie                                |
| therma<br>for all the                             | l Conduc<br>he layers                 | ctivity<br>acc          | y is v<br>cordi      | varie                                |
| therma<br>for all the                             | I Conduc<br>he layers<br>the ma       | tivity<br>acc<br>teria  | y is v<br>cordi      | varie                                |
| therma<br>for all the                             | I Conduc<br>he layers<br>the ma       | tivity<br>acc<br>teria  | y is v<br>cordi<br>I | eplate<br>varie                      |

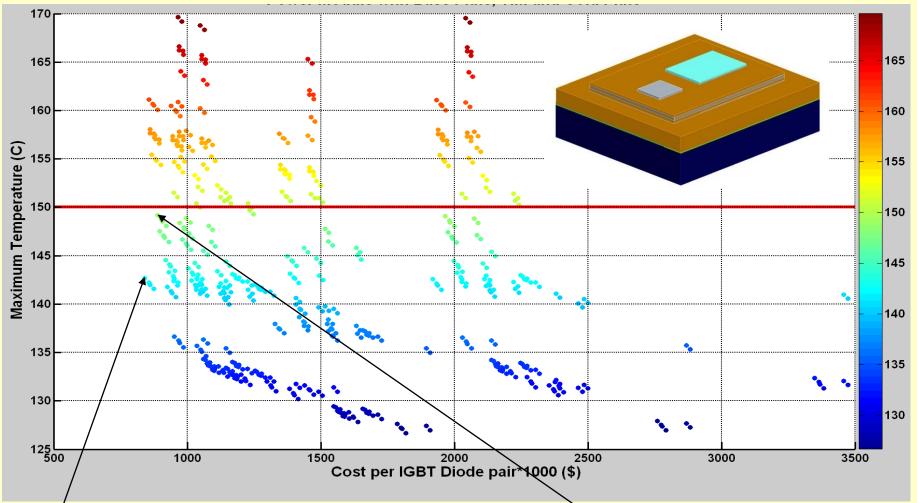


Bulk material costs are assigned on a volumetric basis

Heat Transfer Coefficient = 18,350 W/(m^2.K)

Coolant Temperature = 105 °C

### Materials combination for cost reduction – Topology 1



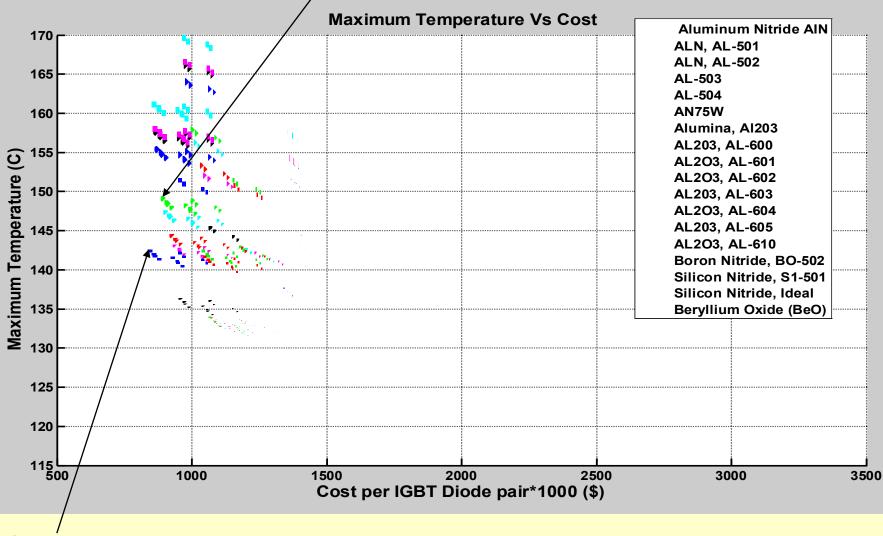
Low-cost combination that meets the performance target (Cu-Mo, Graphite, SiN-Ideal)

Low-cost combination that meets the performance target (Cu-Mo, Graphite, Alumina, an LTCC substrate)

Cost -> 842 Peak Temp -> 142 °C Cost -> 889 Peak Temp -> 149 °C

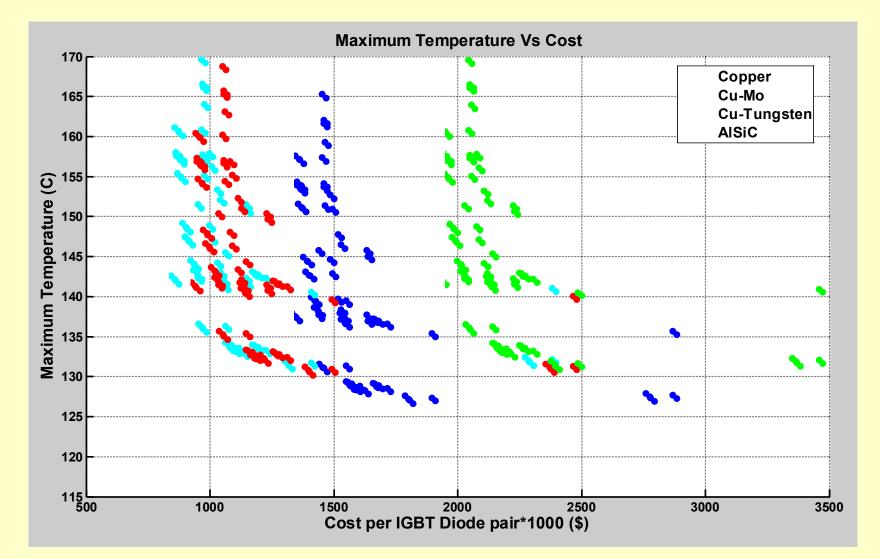
### **Substrate Materials for Cost Reduction – Topology 1**

Alumina, an LTCC substrate



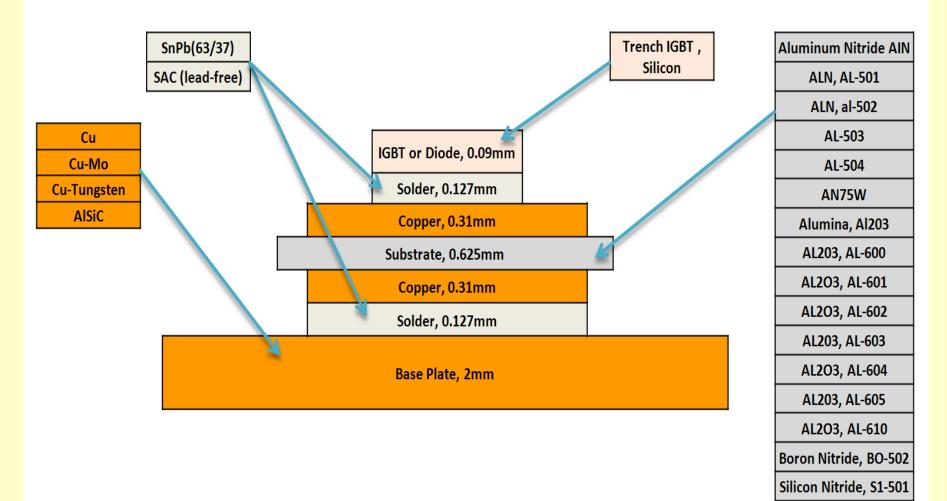
Silicon nitride, ideal

### **Base Plate Materials for Cost Reduction – Topology 1**



Cu-Mo is a candidate base plate material (used in Prius)

# **Materials Exploration – Topology 2**

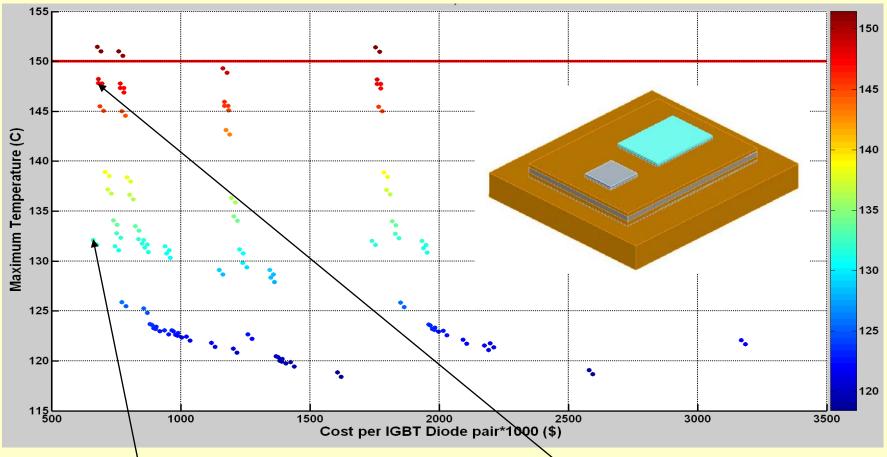


#### **Base Plate Cooling**

Silicon Nitride, Ideal

Beryllium oxide (BeO)

### **Materials Combination for Cost Reduction – Topology 2**



Low-cost combination that meets the performance target (Cu-Mo, SiN-Ideal)

Cost -> 662 Peak Temp -> 132 °C

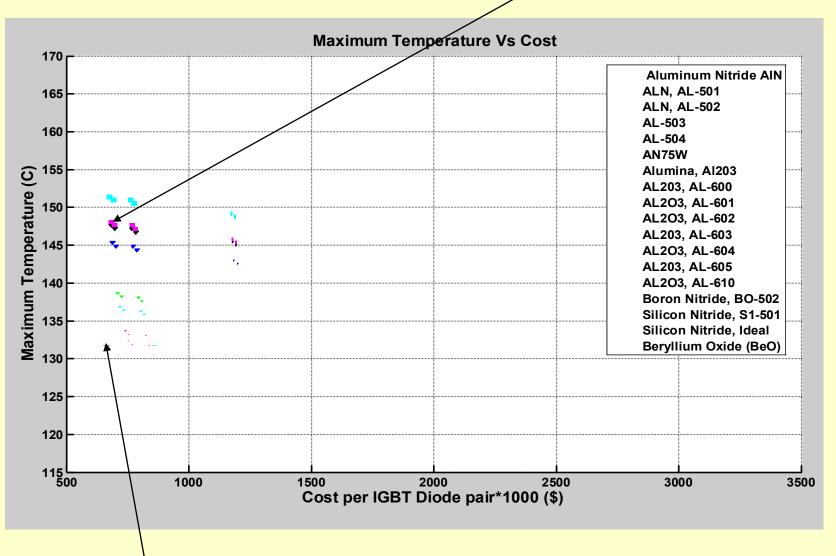
Low-cost combination that meets the performance target (Cu-Mo, Alumina, an LTCC substrate)

Cost -> 682 Peak Temp -> 148 °C

Cost with Topology 1 -> 889

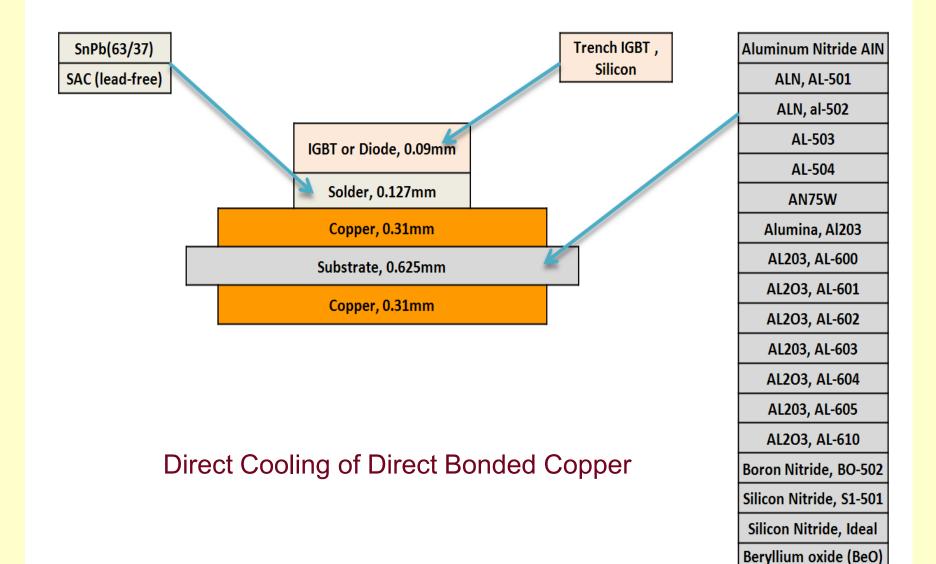
### **Substrate Materials for Cost Reduction – Topology 2**

Alumina, an LTCC substrate

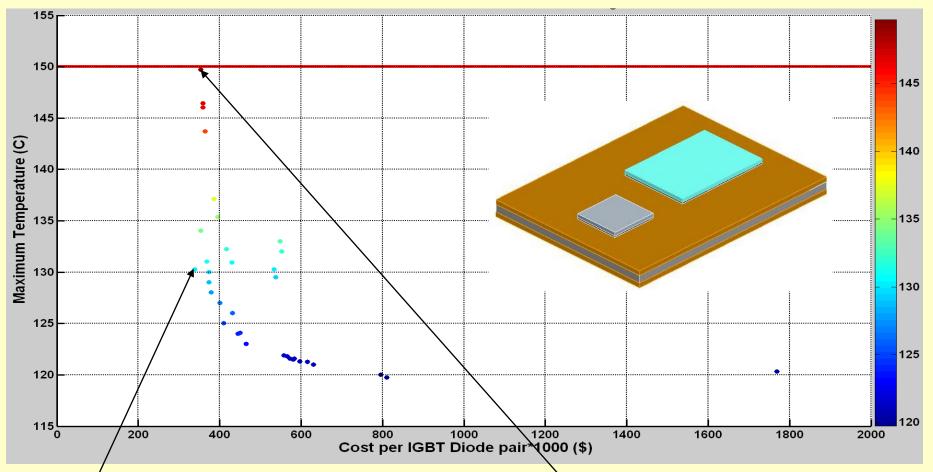


Silicon nitride, ideal

# **Materials Exploration – Topology 3**



### **Materials Combination for Cost Reduction – Topology 3**



Low-cost combination that meets the performance target (SnPb(63/37), SiN-Ideal)

Cost -> 339 Peak Temp -> 130 °C

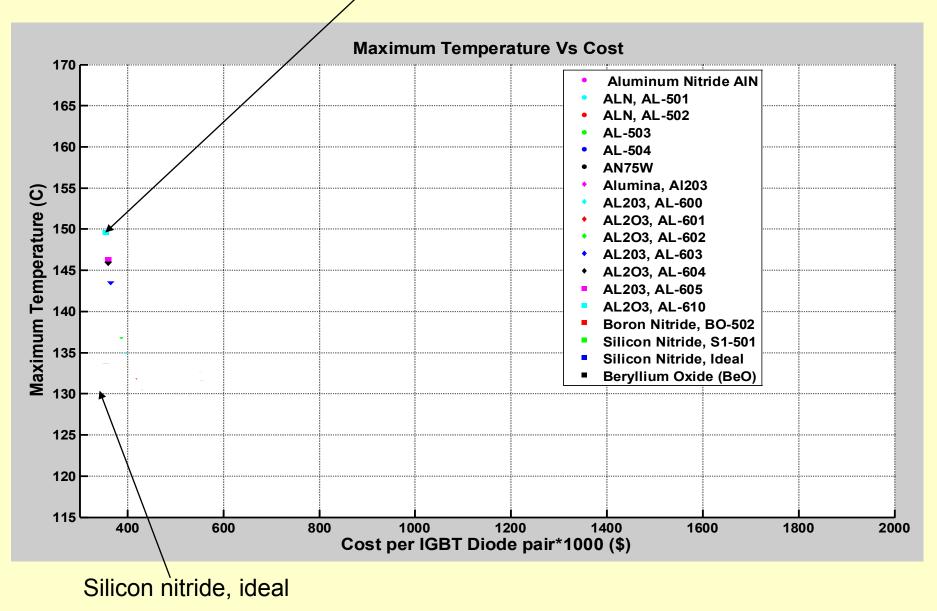
Low-cost combination that meets the performance target (SnPb(63/37), Alumina, an LTCC substrate)

Cost -> 354 Peak Temp -> 149 °C

Topology 1 -> 889, Topology 2 -> 682

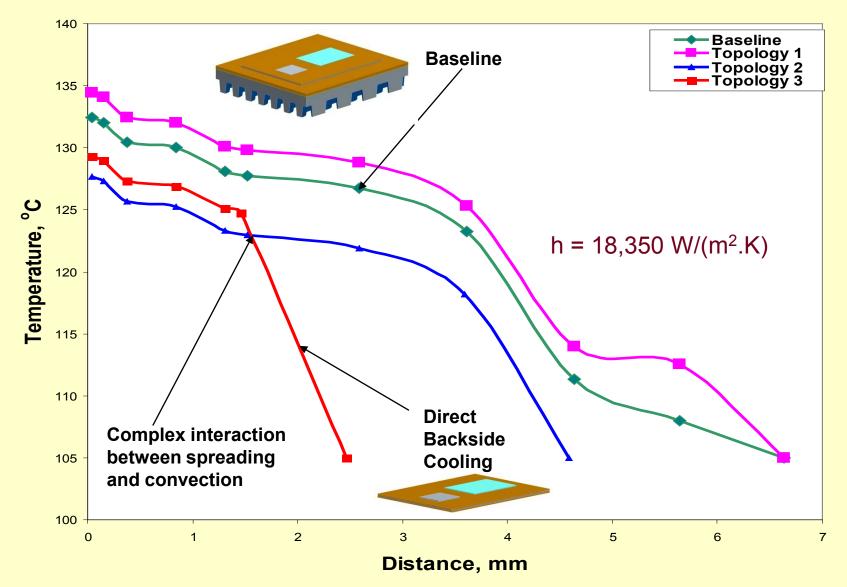
### **Substrate Materials for Cost Reduction – Topology 3**

Alumina, an LTCC substrate

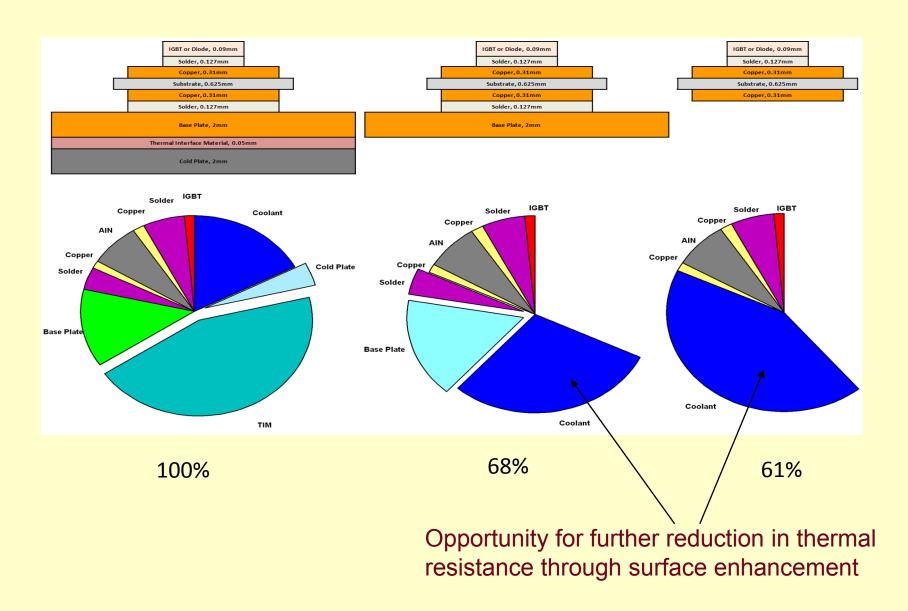


### **Topology Effect on Junction Temperature**

#### **Effect of Topology on Peformance**



# **Thermal Resistances – Contributions**



## **Surface Enhancement**

U = h . A

Targeted surface area enhancement is about 3

 $U = h \cdot 3 A$ 

Effective area would be less than 3. Let's assume it's about 2.2:

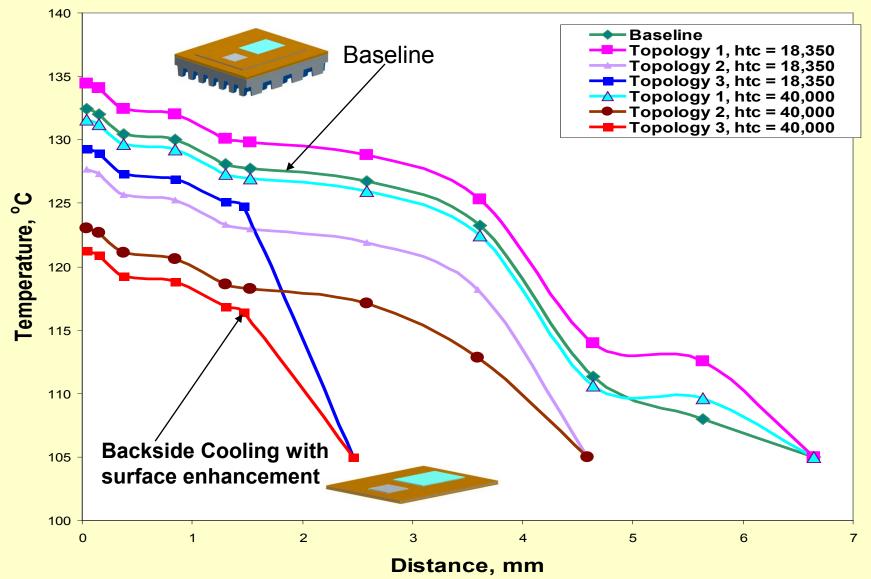
U = h . (2.2 A) (in the test) U = (2.2 h) . A (for modeling purposes)

The assumption above might be all right for a first order approximation:

Baseline, h = 18, 350 W/(m<sup>2</sup>.K) Enhanced, h = 2.2 \* h = 2.2 \* 18, 350 = 40,000 W/(m<sup>2</sup>.K)

### Combined Effects of Topology and Cooling Technology on Junction Temperature





# **Conclusions and Future Studies**

- Advanced thermal control (advanced cooling technologies and novel packaging topologies) helps to meet FreedomCAR program's key target of cost.
- Direct Backside Cooling (Topology 3) has the greatest potential for cost reduction.
- Using Advanced Thermal Control, low-cost LTCC substrate (alumina) has the potential to replace the traditional, more expensive HTCC substrate, AIN.
- Surface enhancement provides further opportunity for performance enhancement.
- Future studies would involve reliability aspects and emerging substrate technologies (LTCC and Organic).

# Acknowledgements

 First author acknowledges the inputs from Andrew A. Wereszczak, Govindarajan Muralidharan (Oak Ridge National Laboratory), Rajen Chanchani (Sandia National Laboratory), Dr. Liangyu Chen (NASA Glenn Research Center) and Prof. Jean-Paul Issi.